

FIG. 1.

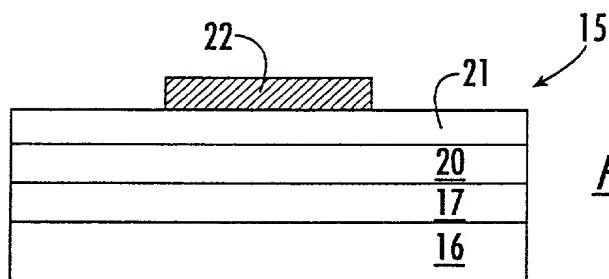


FIG. 2.

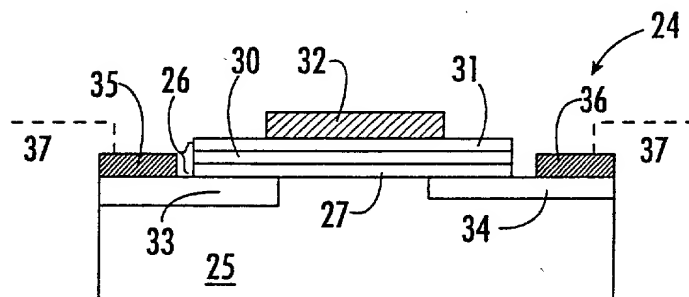


FIG. 3.

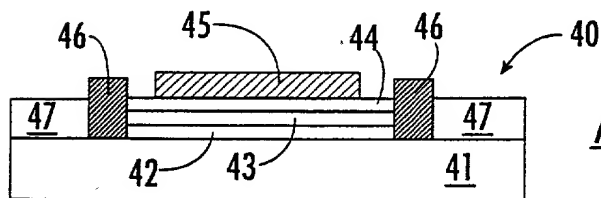


FIG. 4.

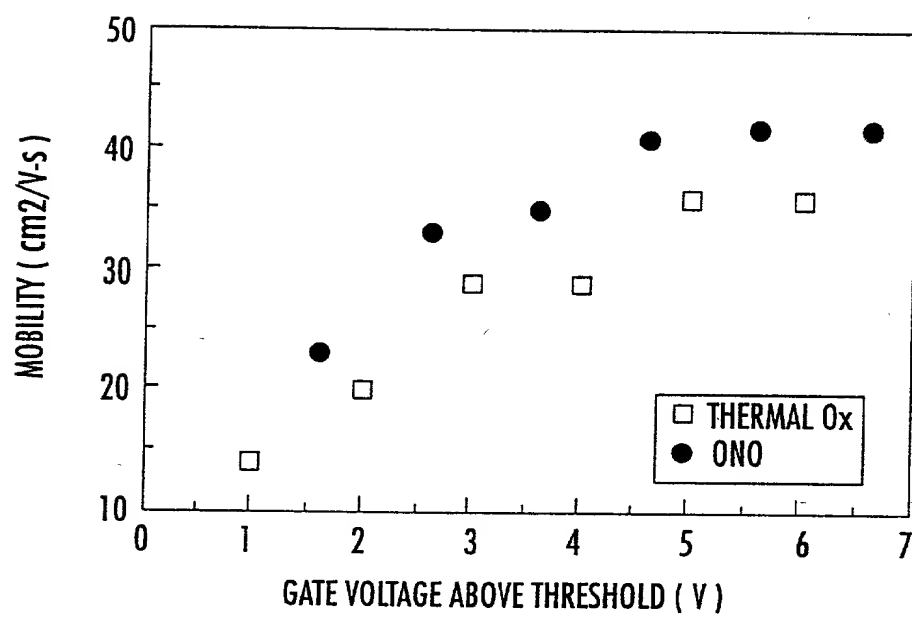


FIG. 5.

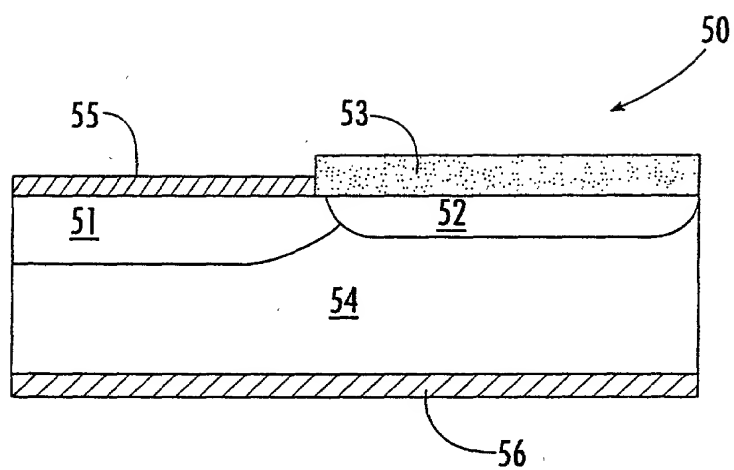


FIG. 6.

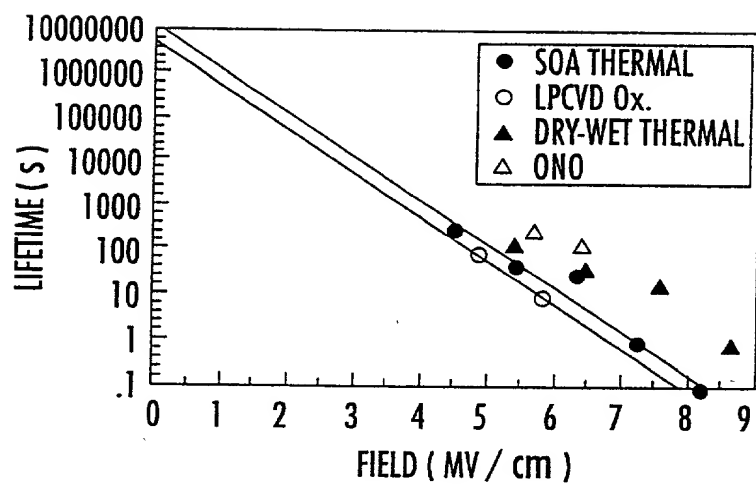


FIG. 7.

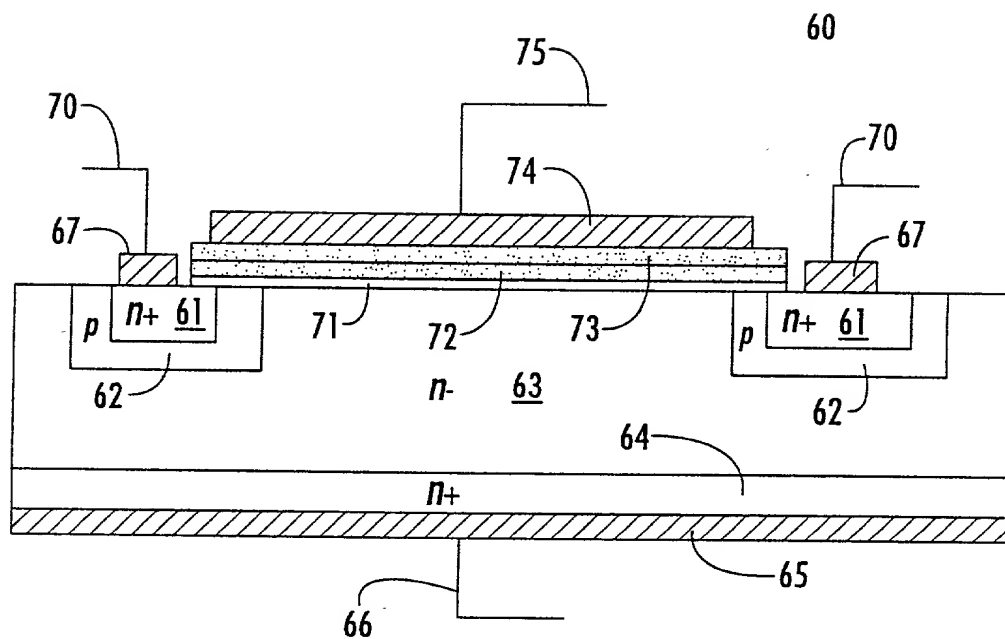


FIG. 8.

Figure 1 is a log-linear plot showing the lifetime (s) versus the electric field (MV/cm) for various SiC devices at 350°C. The y-axis is logarithmic, ranging from 0.1 to 1,000,000 seconds. The x-axis is linear, ranging from 0 to 10 MV/cm. Two parallel lines represent the lifetime degradation for SOA and LPCVD SiC. Data points for SOA THERMAL, DRY-WET THERMAL, LPCVD, ONO, DRY-WET FET, LPCVD FET, and ONO FET are plotted. The lifetime decreases as the electric field increases.

| Device Type | Field (MV/cm) | Lifetime (s) |
|-----------------|---------------|--------------|
| SOA THERMAL | 4.8 | 250 |
| SOA THERMAL | 6.5 | 20 |
| SOA THERMAL | 7.5 | 0.8 |
| SOA THERMAL | 8.2 | 0.1 |
| DRY-WET THERMAL | 3.2 | 200 |
| DRY-WET THERMAL | 5.5 | 80 |
| DRY-WET THERMAL | 6.5 | 30 |
| DRY-WET THERMAL | 7.5 | 12 |
| DRY-WET THERMAL | 8.5 | 0.7 |
| LPCVD | 3.2 | 2000 |
| LPCVD | 4.8 | 70 |
| LPCVD | 5.8 | 7 |
| ONO | 3.2 | 200000 |
| ONO | 5.5 | 200 |
| ONO | 6.5 | 100 |
| ONO | 7.2 | 150 |
| DRY-WET FET | 3.2 | 200 |
| DRY-WET FET | 5.5 | 30 |
| DRY-WET FET | 6.5 | 25 |
| DRY-WET FET | 7.5 | 0.8 |
| DRY-WET FET | 8.5 | 0.7 |
| LPCVD FET | 3.2 | 2000 |
| LPCVD FET | 4.8 | 70 |
| LPCVD FET | 5.8 | 7 |
| ONO FET | 3.2 | 200000 |
| ONO FET | 5.5 | 200 |
| ONO FET | 6.5 | 100 |
| ONO FET | 7.2 | 150 |

FIG. 9.

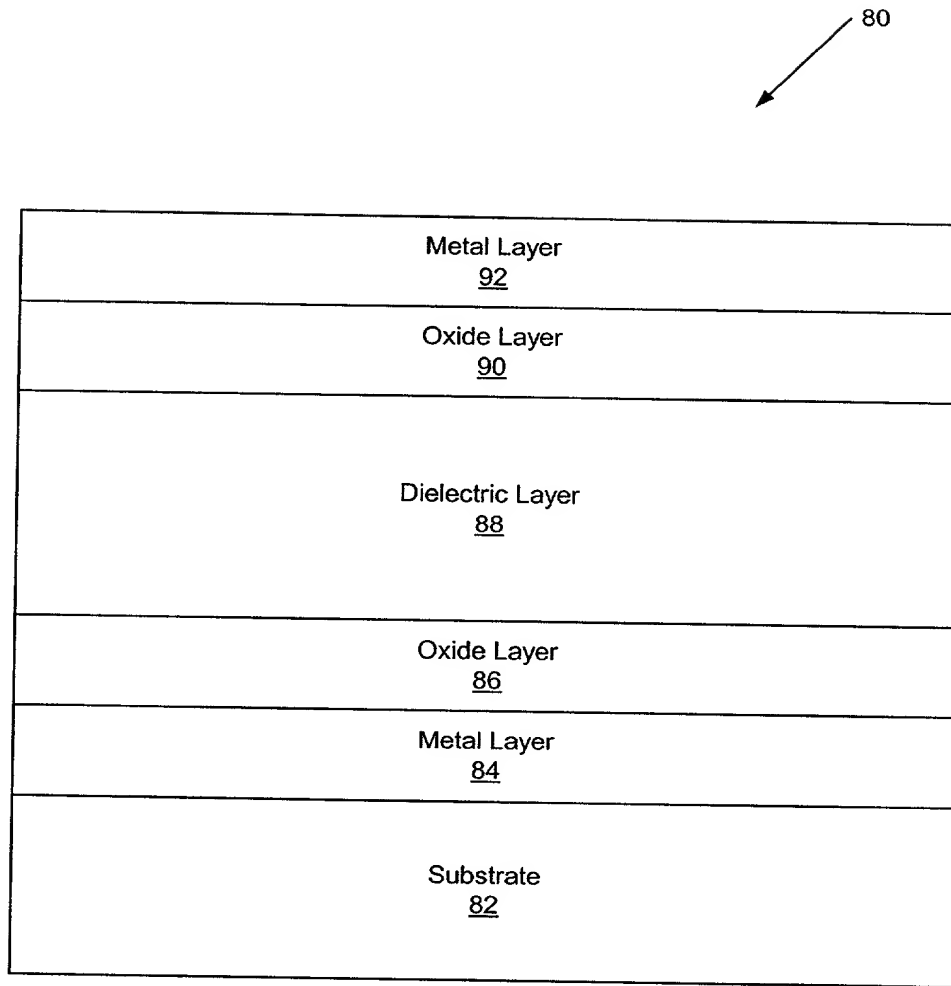


Figure 10

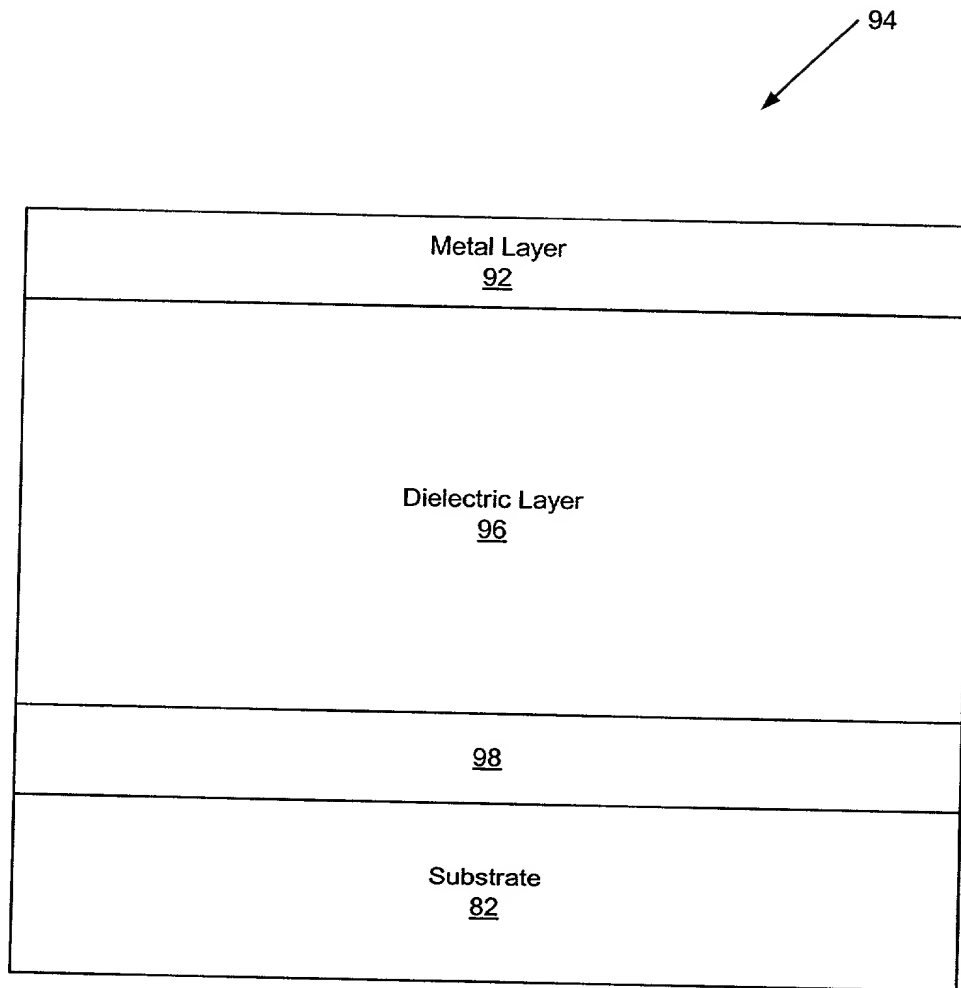


Figure 11

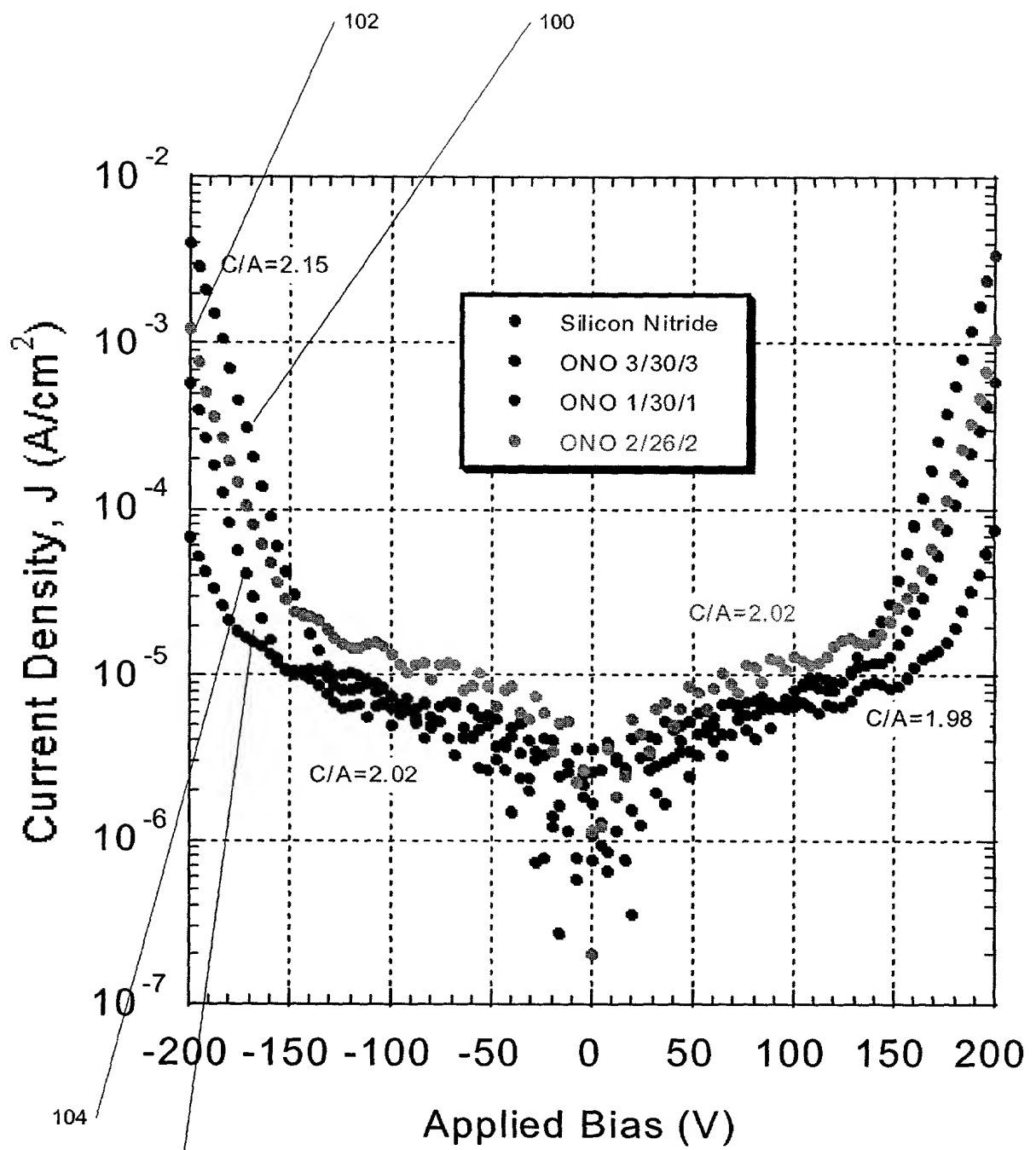


Figure 12

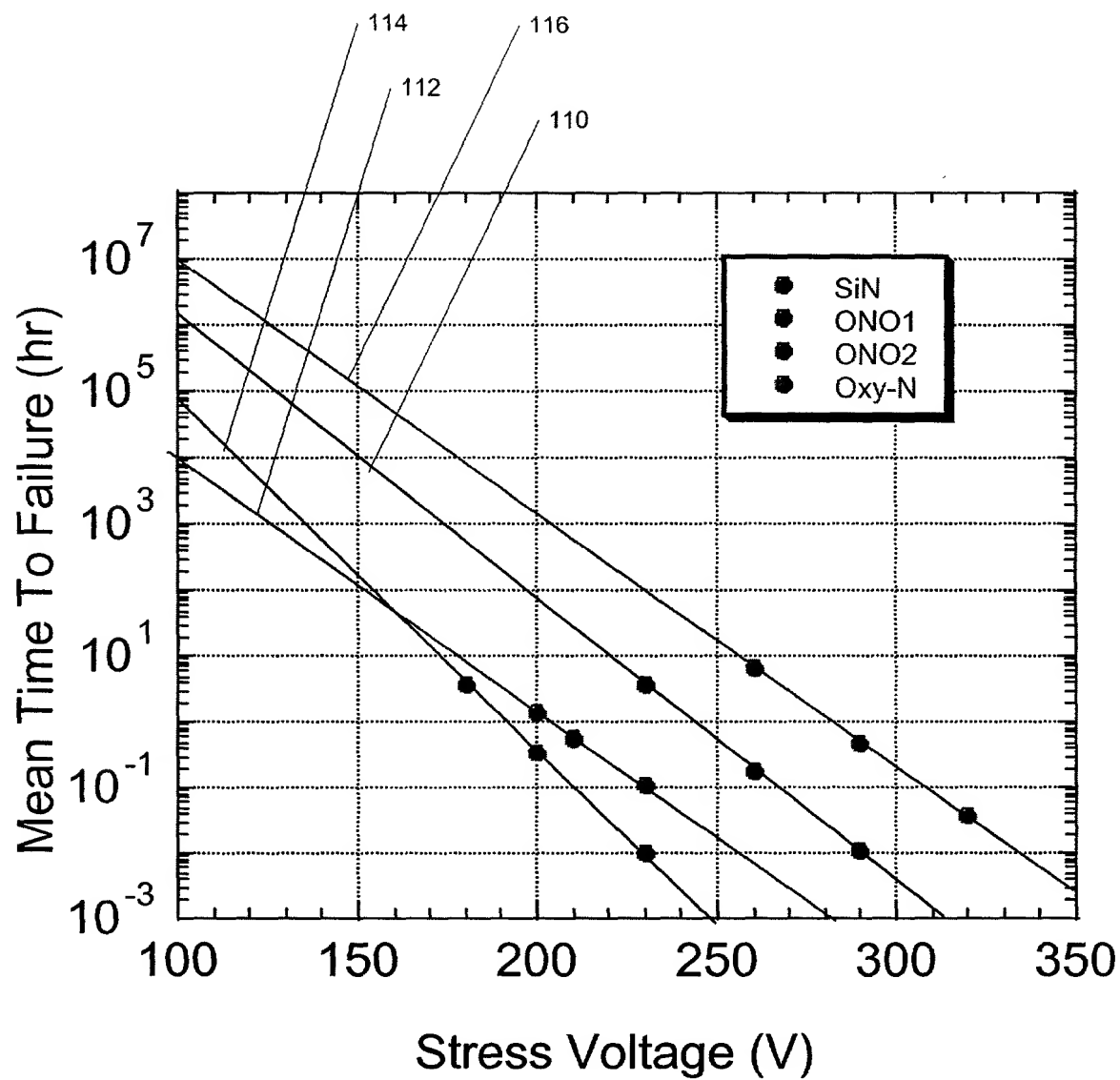


Figure 13

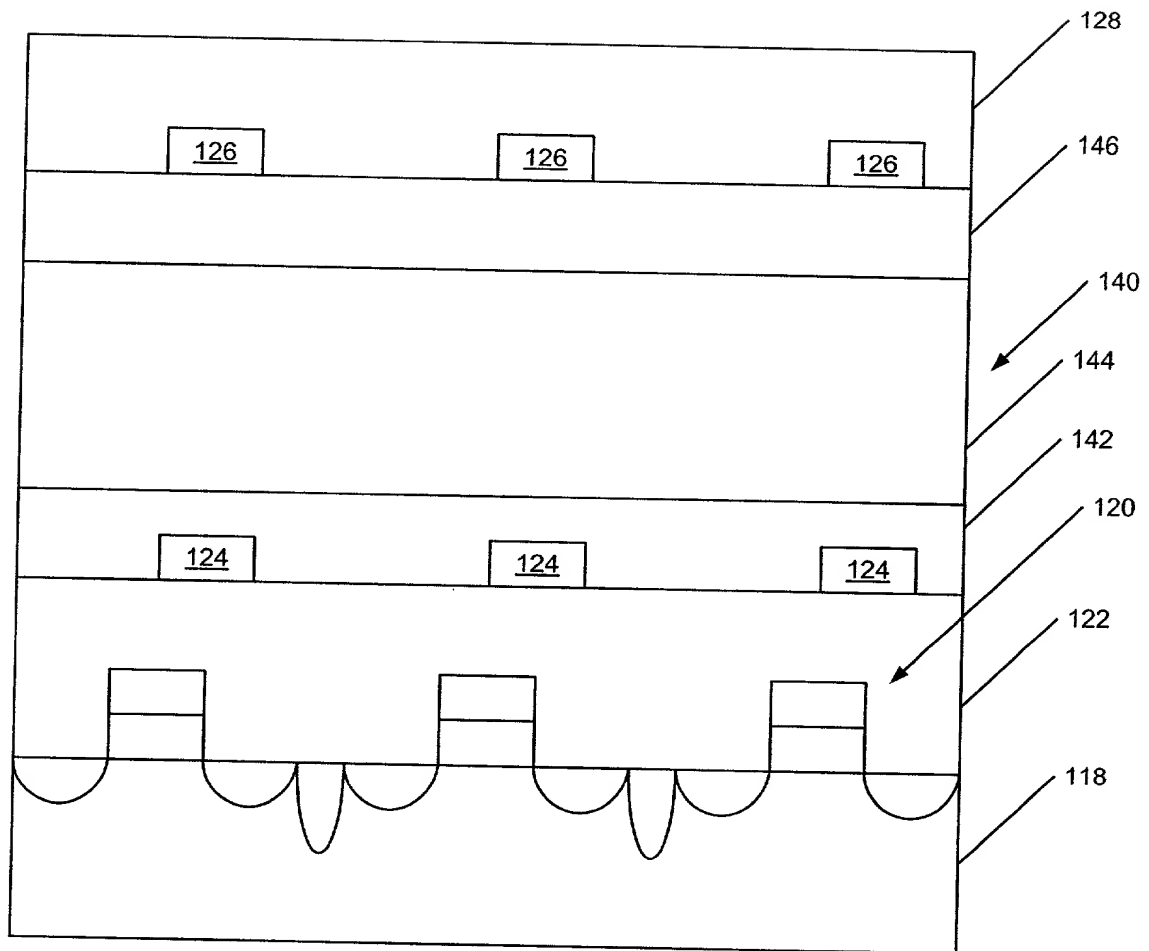


Figure 14